

Product / Process Change Notice

Parts Affected:

Chip process CP716V, PNP high voltage transistors, wafers, and die in chip form.

Extent of Change:

An overall reduction of the die area.

The CP716V chip process currently measures 19.7 x 19.7 mils and is being replaced by the CP736V chip process which measures 17.3 x 17.3 mils.

Reason for Change:

To accommodate assemblies of extremely small surface mount, epoxy molded packages.

Effect of Change:

This change does not affect the electrical characteristics of any device.

Qualification:

Standard evaluation and qualifications completed resulting in no performance differences compared to current product.

Effective Date of Change:

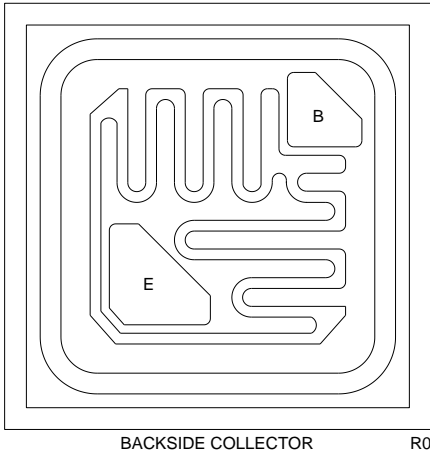
Existing inventory will be shipped until depleted.

Sample Availability:

Please contact Salesperson or Manufacturer's Representative.

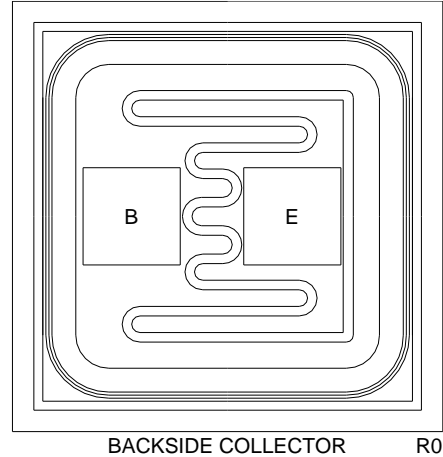
Figures:

Figure 1: CP716V Chip Geometry



Die Size: 20 x 20 mils
Die Thickness: 7.1 mils
Bond Pad Area (Emitter): 4.7 x 4.7 mils
Bond Pad Area (Base): 4 x 4 mils
Topside Metal: Al (30,000Å)
Backside Metal: Au (18,000Å)

Figure 2: CP736V Chip Geometry



Die Size: 17.3 x 17.3 mils
Die Thickness: 7.1 mils
Bond Pad Area (Emitter): 3.9 x 3.9 mils
Bond Pad Area (Base): 3.9 x 3.9 mils
Topside Metal: Al-Si (30,000Å)
Backside Metal: Au (12,000Å)

Part Numbers Affected:

2N5401
2N5400
CMLT5554
CMPT5401
CMPT5401E
CMUT5401
CMUT5401E
CXT5401
CXT5401E
CZT5401
CZT5401E
CEN1154
PN4888
PN4889
CP716V-CEN1254-CT
CP716V-2N3635-CM
CP716V-2N3635-WN
CP716V-2N3637-CT
CP716V-2N5401-CTAN
CP716V-2N5401-WN